VS-HFA08TB120-M3

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ROHS COMPLIANT

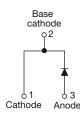
HALOGEN

FREE

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



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PRIMARY CHARACTERISTICS						
I _{F(AV)} 8 A						
V _R	1200 V					
V _F at I _F	2.4 V					
t _{rr} typ.	28 ns					
T _J max.	150 °C					
Package	2L TO-220AC					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRBM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	I _F	T _C = 100 °C	8				
Single pulse forward current	I _{FSM}		130	А			
Maximum repetitive forward current	I _{FRM}		32				
Maximum power dissipation	P _D	T _C = 25 °C	73.5	W			
waximum power dissipation		T _C = 100 °C	29	٧V			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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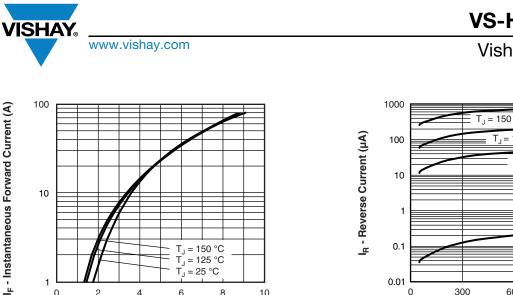
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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-		
		I _F = 8.0 A	-	2.6	3.3	V	
Maximum forward voltage	V _{FM}	I _F = 16 A	-	3.4	4.3		
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1		
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.31	10		
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	135	1000	μA	
Junction capacitance	CT	V _R = 200 V	-	11	20	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/µs, V _R = 30 V	-	28	-	
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95	ns
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	106	160	
Deal and a second	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	A
Peak recovery current	I _{RRM2}	T _J = 125 °C		-	6.2	11	
Poverse resource chorge	Q _{rr1}	T _J = 25 °C		-	140	380	nC
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880	nc
Peak rate of recovery current during $t_{\rm b}$	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/µs
	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-	γγµs

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	1.7		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.25	-		
Weight			-	6.0	-	g	
weight			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style 2L TO-220AC		HFA08	3TB120		



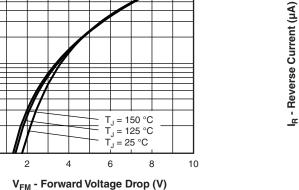


Fig. 1 - Maximum Forward Voltage Drop Characteristics

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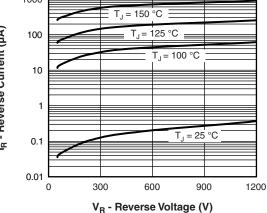


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

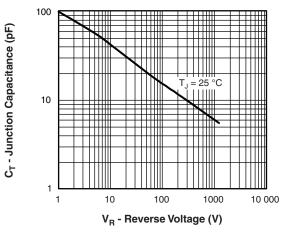


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

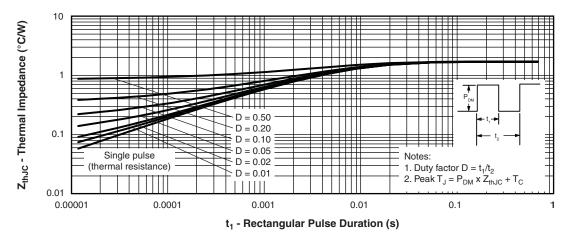


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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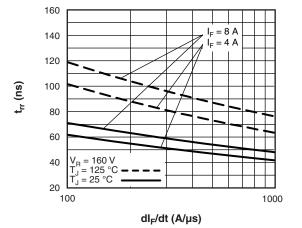


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

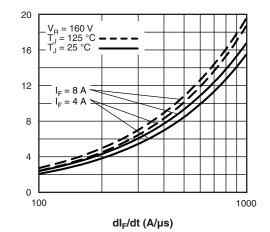
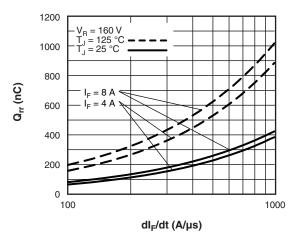


Fig. 6 - Typical Recovery Current vs. dl_F/dt





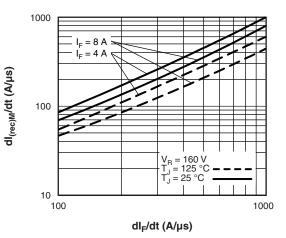


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

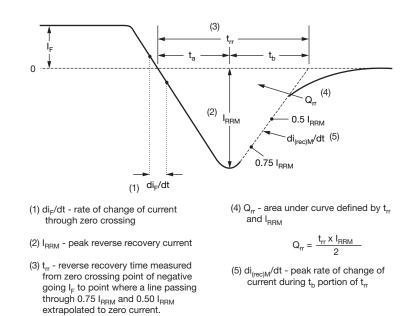


Fig. 9 - Reverse Recovery Waveform and Definitions

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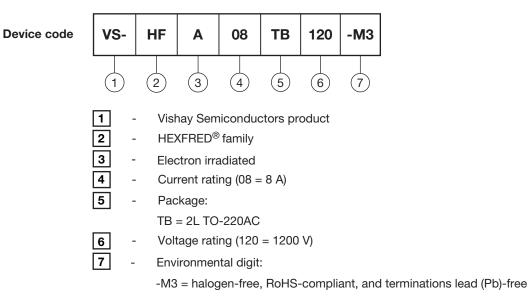
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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA08TB120-M3	50	1000	Antistatic plastic tube				

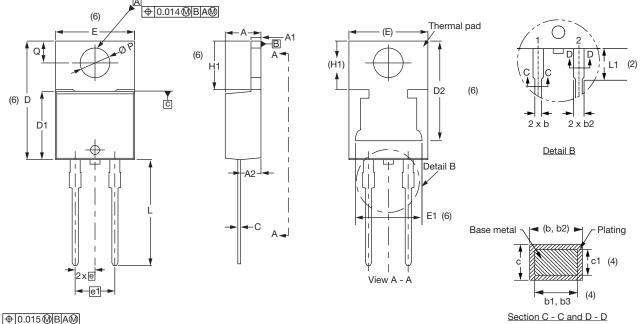
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96156					
Part marking information www.vishay.com/doc?95391					

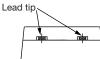


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2L TO-220AC

DIMENSIONS in millimeters and inches





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC®	outline	TO-220AC
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SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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